

FNK N-Channel Enhancement Mode Power MOSFET

Description

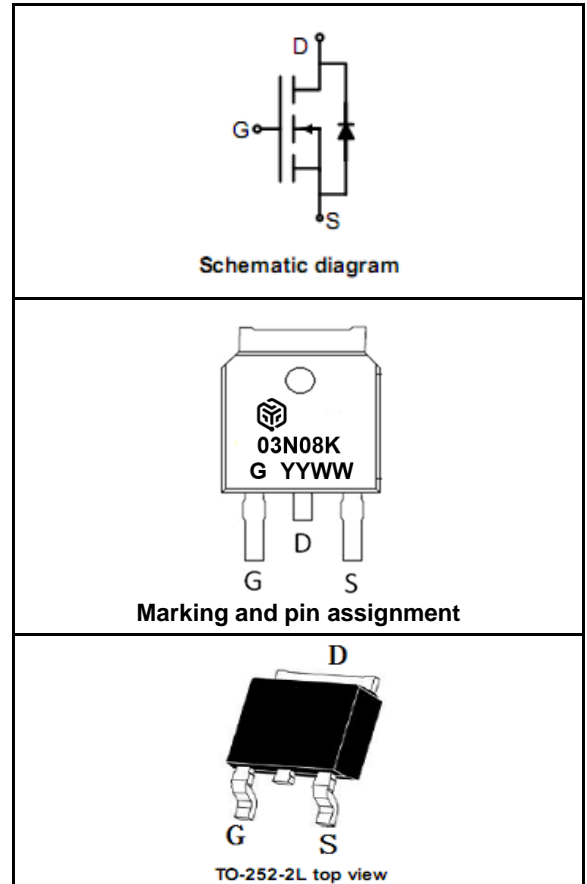
The FNK03N045K uses advanced trench technology and provide excellent $R_{DS(ON)}$ with low gate charge, it can be used in a wide variety of applications.

General Features

- $V_{DS} = 30V, I_D = 80\text{ A}$
 $R_{DS(ON)} < 8.0m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 14m\Omega @ V_{GS}=4.5V$
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply



PACKAGE MARKING AND ORDERING INFORMATION

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|------------|----------------|-----------|------------|----------|
| 03N045K | FNK03N045K | TO -252 | | | |

ABSOLUTE MAXIMUM RATINGS($T_A=25^\circ\text{C}$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|-------------------------|----------|------|
| Drain-Source Voltage | V_{DS} | 30 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous@ Current-Pulsed (Note 1) | $I_D(25^\circ\text{C})$ | 80 | A |
| | I_{DM} | 320 | A |
| Maximum Power Dissipation | P_D | 108 | W |
| Single pulse avalanche energy(Note 5) | EAS | 30 | mJ |

| | | | |
|--|----------------|------------|--------------------|
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 150 | $^{\circ}\text{C}$ |
|--|----------------|------------|--------------------|

THERMAL CHARACTERISTICS

| | | | |
|---|-----------------|------|----------------------|
| Thermal Resistance, Junction-to-Case (Note 2) | $R_{\theta JC}$ | 1.15 | $^{\circ}\text{C/W}$ |
|---|-----------------|------|----------------------|

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

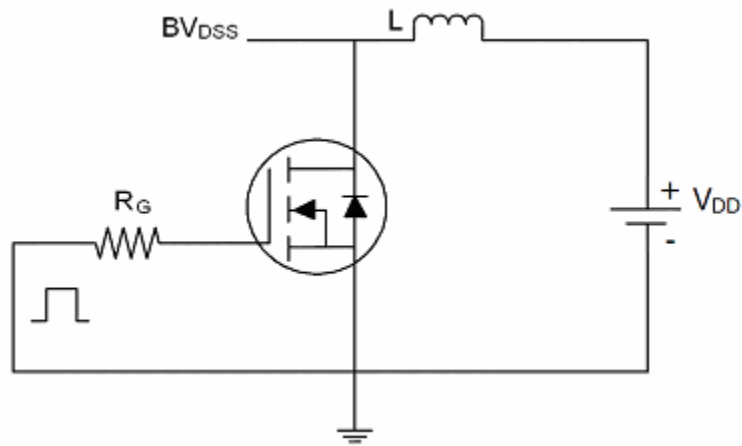
| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|------------------------------------|---------------------|---|------|------|------|------|
| OFF CHARACTERISTICS | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250μA | 30 | | | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =30V, V _{GS} =0V | | | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V, V _{DS} =0V | | | ±100 | nA |
| ON CHARACTERISTICS (Note 3) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μA | 1.08 | 1.65 | 2.38 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =10A | | 5.5 | 8.0 | mΩ |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =4.5V, I _D =6A | | 7.5 | 14 | mΩ |
| DYNAMIC CHARACTERISTICS (Note4) | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =15V, V _{GS} =0V, F=1.0MHz | | 1200 | | PF |
| Output Capacitance | C _{oss} | | | 200 | | PF |
| Reverse Transfer Capacitance | C _{rss} | | | 130 | | PF |
| SWITCHING CHARACTERISTICS (Note 4) | | | | | | |
| Delay Time | t _{d(on)} | V _{DS} =15V, V _{DS} =15V, R _{GEN} =6Ω R _L =1Ω, I _D =14A | | 3 | | nS |
| Turn-on Rise Time | t _r | | | 80 | | nS |
| Turn-Off Delay Time | t _{d(off)} | | | 30 | | nS |
| Turn-Off Fall Time | t _f | | | 10 | | nS |
| Total Gate Charge | Q _g | V _{DS} =15V, I _D =20A, V _{GS} =15V | | 26 | | nC |
| Gate-Source Charge | Q _{gs} | | | 11 | | nC |
| Gate-Drain Charge | Q _{gd} | | | 9 | | nC |
| DRAIN-SOURCE DIODE CHARACTERISTICS | | | | | | |
| Diode Forward Voltage (Note 3) | V _{SD} | V _{GS} =0V, I _S =40A | | | 1.2 | V |
| Diode Forward Current (Note 2) | I _S | | | | 40 | A |
| Reverse Recovery Time | trr | T _J = 25℃, I _F =1A di/dt = 100A/us (Note3) | | 78 | | ns |
| Reverse Recovery Charge | Qrr | | | 51 | | nc |

NOTES:

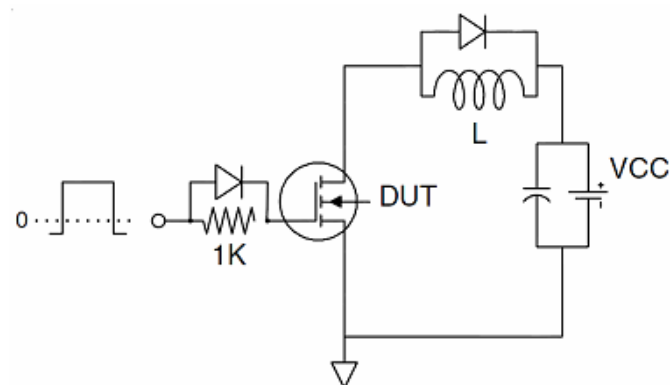
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on 1in² FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production testing
5. EAS condition $T_J=25^{\circ}\text{C}, V_{DD}=15V, V_G=10V, L=0.5mH, R_g=25$

Test circuit

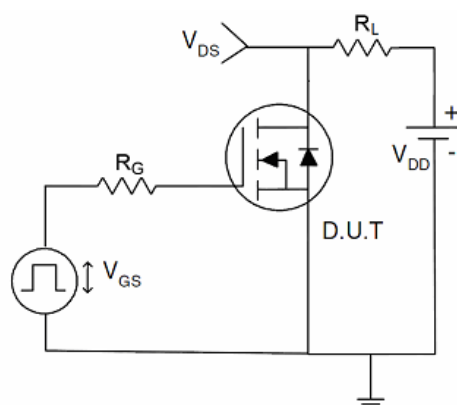
1) EAS test Circuits

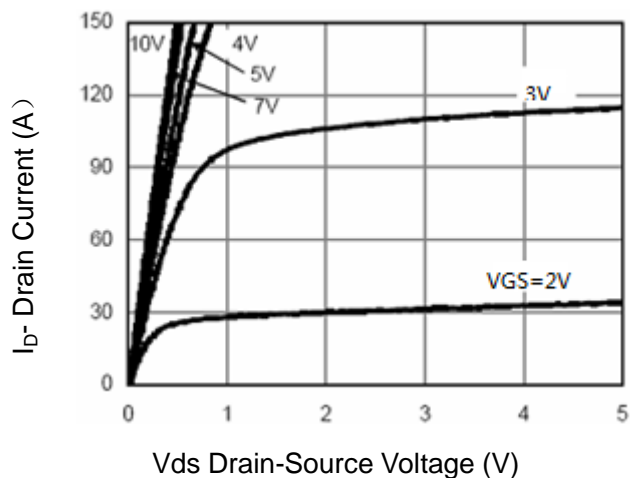
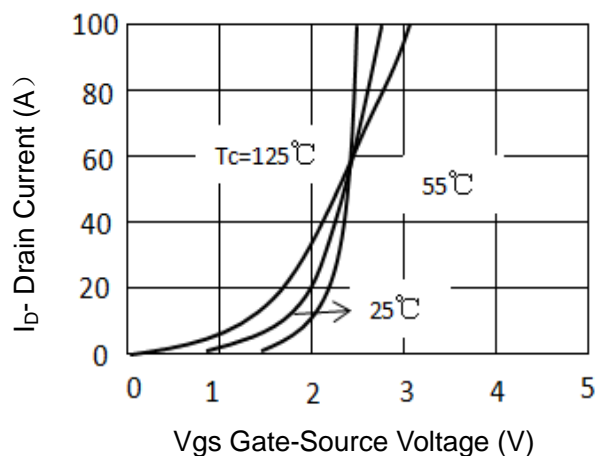
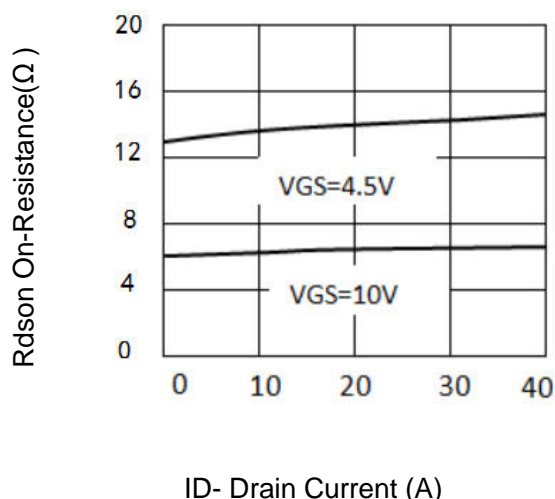
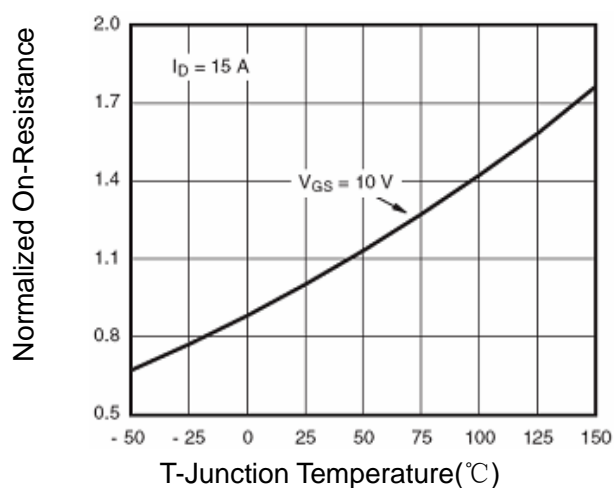
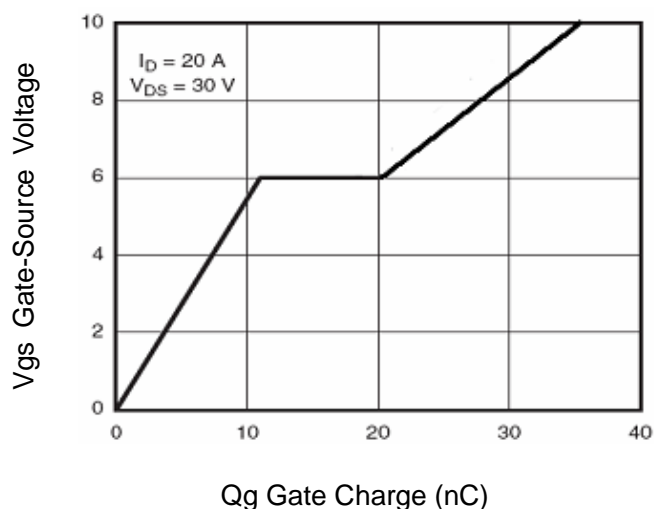
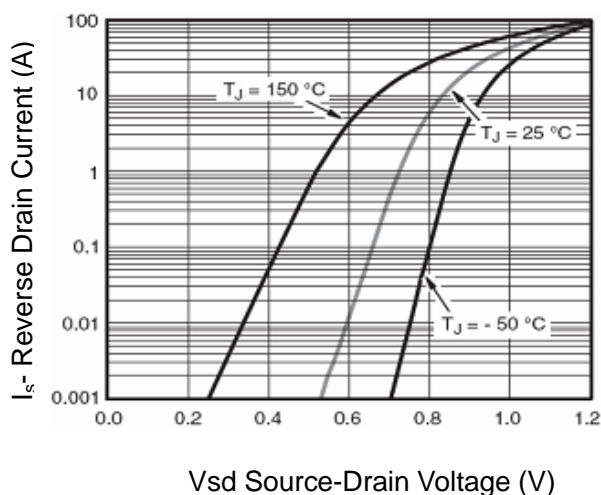


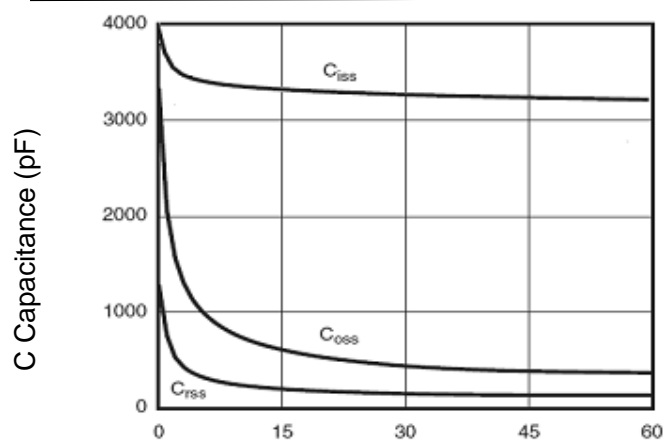
2) Gate charge test Circuit



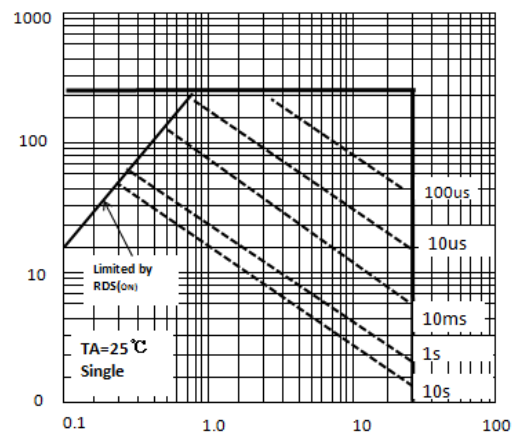
3) Switch Time Test Circuit



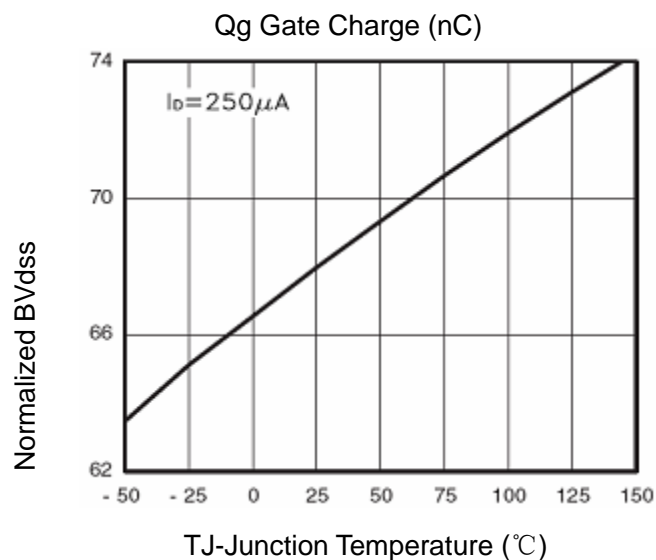
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 1 Output Characteristics

Figure 2 Transfer Characteristics

Figure 3 Drain-Source On-Resistance

Figure 4 RDSON-Junction Temperature

Figure 5 Gate Charge

Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

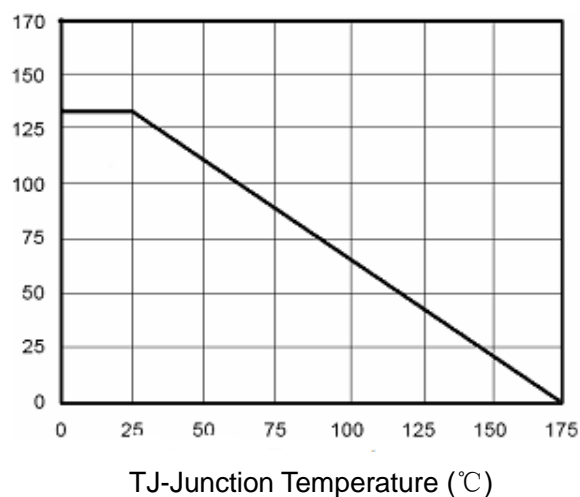
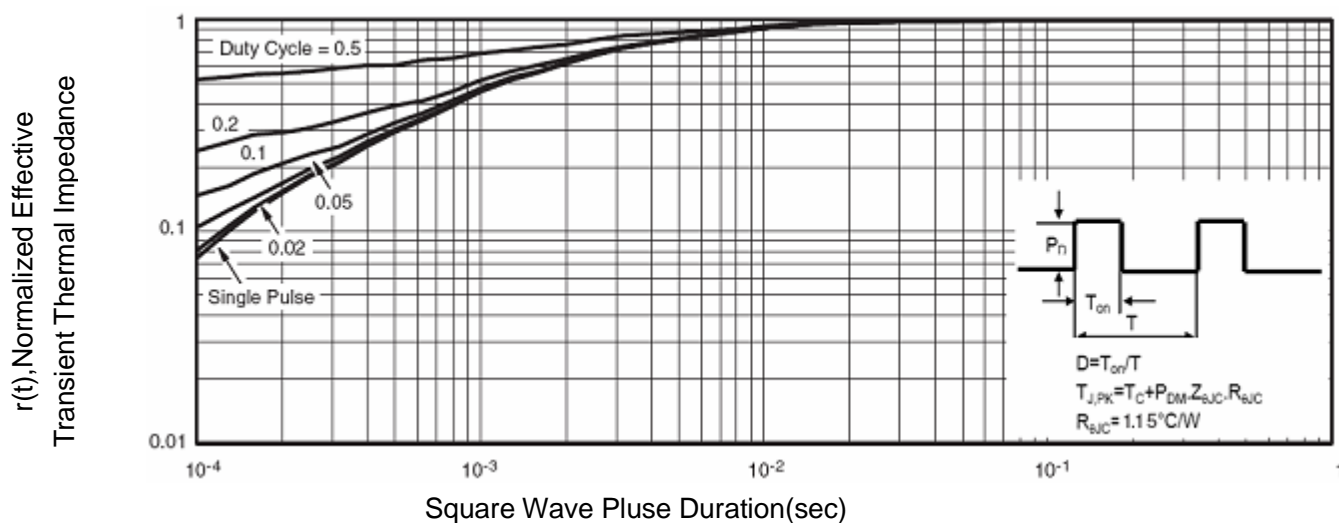
ID- Drain Current (A)


Figure 8 Safe Operation Area

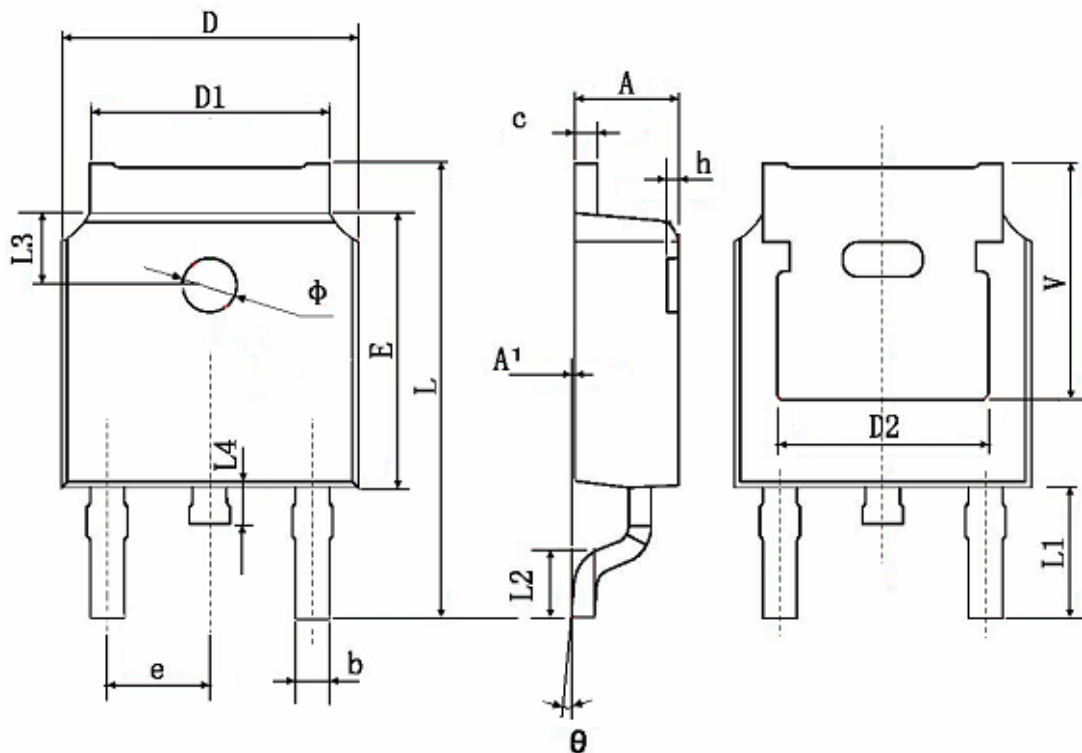
Vds Drain-Source Voltage (V)


Figure 9 BVDSS vs Junction Temperature

Power Dissipation (w)


Figure 10 Power De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252 PACKAGE INFORMATION



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|----------|---------------------------|--------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 2.200 | 2.400 | 0.087 | 0.094 |
| A1 | 0.000 | 0.127 | 0.000 | 0.005 |
| b | 0.660 | 0.860 | 0.026 | 0.034 |
| c | 0.460 | 0.580 | 0.018 | 0.023 |
| D | 6.500 | 6.700 | 0.256 | 0.264 |
| D1 | 5.100 | 5.460 | 0.201 | 0.215 |
| D2 | 4.830 TYP. | | 0.190 TYP. | |
| E | 6.000 | 6.200 | 0.236 | 0.244 |
| e | 2.186 | 2.386 | 0.086 | 0.094 |
| L | 9.800 | 10.400 | 0.386 | 0.409 |
| L1 | 2.900 TYP. | | 0.114 TYP. | |
| L2 | 1.400 | 1.700 | 0.055 | 0.067 |
| L3 | 1.600 TYP. | | 0.063 TYP. | |
| L4 | 0.600 | 1.000 | 0.024 | 0.039 |
| ϕ | 1.100 | 1.300 | 0.043 | 0.051 |
| θ | 0° | 8° | 0° | 8° |
| h | 0.000 | 0.300 | 0.000 | 0.012 |
| V | 5.350 TYP. | | 0.211 TYP. | |

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